

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Tuller et al. **GROUP:** Unknown
SERIAL NO: Unknown **EXAMINER:** Unknown
FILED: Herewith
FOR: METHOD FOR P-TYPE DOPING WIDE BAND GAP OXIDE
SEMICONDUCTORS

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that is required.

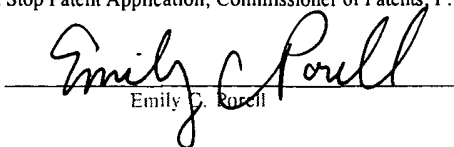
Respectfully submitted,



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CERTIFICATE OF EXPRESS MAIL UNDER 37 C.F.R. §1.10

I hereby certify that this Information Disclosure Statement and the documents referred to as enclosed therein are being deposited with the United States Postal Service on **September 16, 2003** in an envelope as "Express Mail Post Office to Addressee" Mailing Label Number **EV271854011US** addressed to the: Mail Stop Patent Application, Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450.



Emily C. Powell

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

MIT.9983
ATTORNEY DOCKET NO.

APPLICANT: Tuller et al.

FILING DATE: Herewith

Unknown
SERIAL NO.

GROUP: Unknown

EXAMINER: Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AJ						
	AK						
	AL						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AM	"Production and Properties of p-n Junctions in Reactively Sputtered ZnO," Tuzemen et al. <i>Physica B</i> . 2001. Elsevier Science.
	AN	"Fabrication of the low-resistive p-type ZnO by codoping method," Joseph et al. <i>Physica B</i> . 2001. Elsevier Science.
	AO	"Pulsed Laser reactive deposition of p-type ZnO film enhanced by an electron cyclotron resonance source," Guo et al. <i>Journal of Crystal Growth</i> . 2001. Elsevier Science.

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.